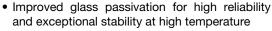


# Medium Power Phase Control Thyristors (Stud Version), 10 A



PRIMARY CHARACTERISTICS				
I <sub>T(AV)</sub>	10 A			
V <sub>DRM</sub> /V <sub>RRM</sub>	100 V, 200 V, 400 V, 600 V, 800 V, 1000 V, 1200 V			
V <sub>TM</sub>	1.75 V			
I <sub>GT</sub>	60 mA			
T <sub>J</sub>	-65 °C to +125 °C			
Package	TO-48 (TO-208AA)			
Circuit configuration	Single SCR			

#### **FEATURES**





- High dI<sub>F</sub>/dt and dV/dt capabilities
- Standard package
- · Low thermal resistance
- · Metric threads version available
- Types up to 1200 V V<sub>DRM</sub>/V<sub>RRM</sub>
- Designed and qualified for industrial and consumer level
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>

#### **TYPICAL APPLICATIONS**

- Medium power switching
- · Phase control applications

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
		10	Α		
I <sub>T(AV)</sub>	T <sub>C</sub>	85	°C		
I <sub>T(RMS)</sub>		25	Α		
I <sub>TSM</sub>	50 Hz	225	^		
	60 Hz	240	A		
l <sup>2</sup> t	50 Hz	255	A2-		
	60 Hz	233	A <sup>2</sup> s		
V <sub>DRM</sub> /V <sub>RRM</sub>		100 to 1200	V		
t <sub>q</sub>	Typical	110	μs		
T <sub>J</sub>		-65 to +125	°C		

#### **ELECTRICAL SPECIFICATIONS**

VOLTAGE RATINGS							
TYPE NUMBER	VOLTAGE CODE	V <sub>DRM</sub> /V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE <sup>(1)</sup> V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK VOLTAGE <sup>(2)</sup> V	$I_{DRM}/I_{RRM}$ MAXIMUM AT T <sub>J</sub> = T <sub>J</sub> MAXIMUM mA			
	10	100	150	20			
	20	200	300				
	40	400	500				
VS-10RIA	60	600	700	10			
	80	800	900	10			
	100	1000	1100				
	120	1200	1300				

#### Notes

<sup>(1)</sup> Units may be broken over non-repetitively in the off-state direction without damage, if dl/dt does not exceed 20 A/µs

<sup>(2)</sup> For voltage pulses with  $t_p \le 5 \text{ ms}$ 



ABSOLUTE MAXIMUM RAT	TINGS					
PARAMETER	SYMBOL		TEST COND	ITIONS	VALUES	UNITS
Maximum average on-state current	I	190° conducti	on, half sine wave		10	Α
at case temperature	I <sub>T(AV)</sub>	100 Conducti	on, nan sine wave		85	°C
Maximum RMS on-state current	I <sub>T(RMS)</sub>				25	Α
		t = 10 ms	No voltage		225	
Maximum peak, one-cycle	L	t = 8.3 ms	reapplied		240	Α
non-repetitive surge current	I <sub>TSM</sub>	t = 10 ms	100 % V <sub>RRM</sub>		190	A A <sup>2</sup> s
		t = 8.3 ms	reapplied	Sinusoidal half wave,	200	
Maximum I <sup>2</sup> t for fusing		t = 10 ms	No voltage reapplied	initial $T_J = T_J$ maximum	255	
	l <sup>2</sup> t	t = 8.3 ms			233	
		t = 10 ms	100 % V <sub>RRM</sub> reapplied		180	
		t = 8.3 ms			165	
Maximum I <sup>2</sup> √t for fusing	I²√t	t = 0.1 to 10 ms, no voltage reapplied		2550	A²√s	
Low level value of threshold voltage	V <sub>T(TO)1</sub>	(16.7 % x $\pi$ x $I_{T(AV)}$ < I < $\pi$ x $I_{T(AV)}$ ), $T_J = T_J$ maximum		1.10	V	
High level value of threshold voltage	V <sub>T(TO)2</sub>	$(I > \pi \times I_{T(AV)}),$	$T_J = T_J \text{ maximum}$		1.39	V
Low level value of on-state slope resistance	r <sub>t1</sub>	(16.7 % x $\pi$ x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$ ), $T_J = T_J$ maximum		24.3	mΩ	
High level value of on-state slope resistance	r <sub>t2</sub>	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$		16.7	11152	
Maximum on-state voltage	$V_{TM}$	$I_{pk} = 32 \text{ A}, T_J = 25 ^{\circ}\text{C}, t_p = 10 \text{ ms sine pulse}$		1.75	V	
Maximum holding current	I <sub>H</sub>	T. = 25 °C 22	odo supply 12 V ro	esistivo load	130	mA
Typical latching current	ΙL	1j = 25 C, all	ode supply 12 V re	SISTING TOAU	200	mA

SWITCHING					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
	$V_{DRM} \le 600 \text{ V}$			200	
Maximum rate of rise	V <sub>DRM</sub> ≤ 800 V	.11. /.11	$T_J = T_J$ maximum, $V_{DM} = Rated V_{DRM}$ It Gate pulse = 20 V, 15 $\Omega$ , $t_p = 6 \mu s$ , $t_r = 0.1 \mu s$ maximum $I_{TM} = (2 \text{ x rated dl/dt}) A$	180	A/μs
of turned-on current $V_{I}$	V <sub>DRM</sub> ≤ 1000 V	dl <sub>F</sub> /dt		160	
	V <sub>DRM</sub> ≤ 1600 V	, , , , , , , , , , , , , , , , , , , ,		150	
Typical turn-on time		t <sub>gt</sub>	$T_J = 25$ °C, at rated $V_{DRM}/V_{RRM}$ , $T_J = 125$ °C	0.9	
Typical reverse recovery time		t <sub>rr</sub>	$T_J = T_J$ maximum, $I_{TM} = I_{T(AV)}$ , $t_p > 200 \mu s$ , $dI_F/dt = -10 A/\mu s$	4	μs
Typical turn-off time		tq	$T_J = T_J$ maximum, $I_{TM} = I_{T(AV)}$ , $t_p > 200~\mu$ s, $V_R = 100~V$ , $dI_F/dt = -10~A/\mu$ s, $dV/dt = 20~V/\mu$ s linear to 67 % $V_{DRM}$ , gate bias 0 V to 100 W	110	μο

#### Note

•  $t_q = 10 \mu s$  up to 600 V,  $t_q = 30 \mu s$  up to 1600 V available on special request

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise dV/dt	$T_J = T_J$ maximum linear to 100 % rated $V_{DRM}$	100	V/µs	
of off-state voltage	uv/ut	$T_J = T_J$ maximum linear to 67 % rated $V_{DRM}$	300 (1)	ν/μ5

#### Note

 $^{(1)}$  Available with:  $dV/dt = 1000 V/\mu s$ , to complete code add S90 i.e. 10RIA120S90



TRIGGERING					
PARAMETER	SYMBOL	TE	ST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P <sub>GM</sub>	T - T movimum		8.0	W
Maximum average gate power	P <sub>G(AV)</sub>	$T_J = T_J$ maximum		2.0	۷V
Maximum peak positive gate current	$I_{GM}$	$T_J = T_J$ maximum		1.5	Α
Maximum peak negative gate voltage	-V <sub>GM</sub>	$T_J = T_J$ maximum		10	V
DC gate current required to trigger	I <sub>GT</sub>	T <sub>J</sub> = -65 °C	Maximum required gate trigger current/voltage are the lowest value which will trigger all units 6 V anode to cathode applied	90	mA
		T <sub>J</sub> = 25 °C		60	
		T <sub>J</sub> = 125 °C		35	
	V <sub>GT</sub>	T <sub>J</sub> = -65 °C		3.0	V
DC gate voltage required to trigger		T <sub>J</sub> = 25 °C		2.0	
		T <sub>J</sub> = 125 °C		1.0	
DC gate current not to trigger	$I_{GD}$	T <sub>J</sub> = T <sub>J</sub> maximum, V <sub>DRM</sub> = Rated value		2.0	mA
DC gate voltage not to trigger	$V_GD$	$T_J = T_J$ maximum, $V_{DRM} = Rated value$	Maximum gate current/voltage not to trigger is the maximum value which will not trigger any unit with rated V <sub>DRM</sub> anode to cathode applied	0.2	V

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES		UNITS	
Maximum operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65 to +125		°C	
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	DC operation	1.85		K/W	
Maximum thermal resistance, case to heat sink	R <sub>thCS</sub>	Mounting surface, smooth, flat and greased 0.35		35	IV VV	
			TO NUT	TO DEVICE		
			20 (27.5)	25	lbf ⋅ in	
Mounting torque		Lubricated threads (Non-lubricated threads)	0.23 (0.32)	0.29	kgf · m	
		(1011)021104104 111104409)	2.3 (3.1)	2.8	N·m	
Approximate weight			1	4	g	
Approximate weight			0.	49	oz.	
Case style		See dimensions - link at the end of datasheet	TO	)-48 (TO-208A	A)	

△R <sub>thJC</sub> CONDUCTION				
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.44	0.32		
120°	0.53	0.56		
90°	0.68	0.75	$T_J = T_J$ maximum	K/W
60°	1.01	1.05		
30°	1.71	1.73		

#### Note

• The table above shows the increment of thermal resistance RthJC when devices operate at different conduction angles than DC

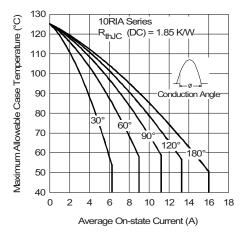


Fig. 1 - Current Ratings Characteristics

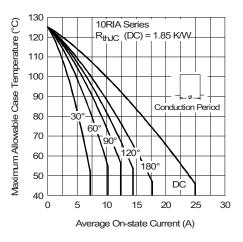


Fig. 2 - Current Ratings Characteristics

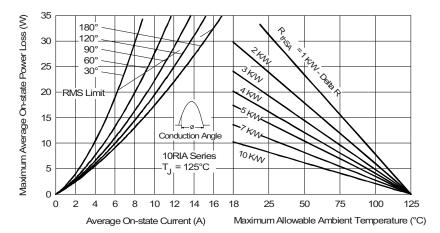


Fig. 3 - On-State Power Loss Characteristics

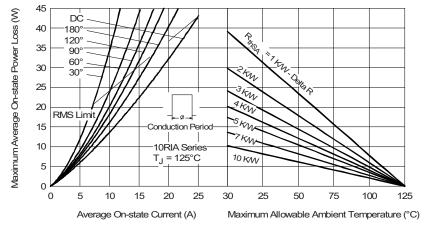


Fig. 4 - On-State Power Loss Characteristics



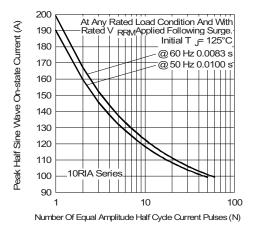


Fig. 5 - Maximum Non-Repetitive Surge Current

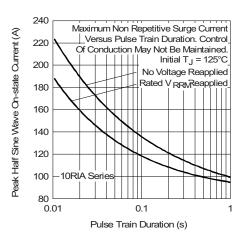


Fig. 6 - Maximum Non-Repetitive Surge Current

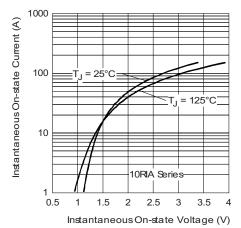


Fig. 7 - Forward Voltage Drop Characteristics

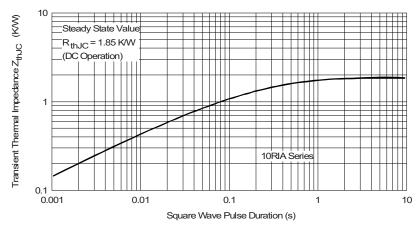


Fig. 8 - Thermal Impedance  $Z_{thJC}$  Characteristics



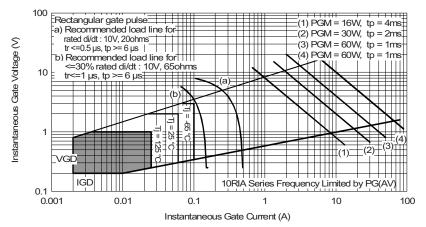


Fig. 9 - Gate Characteristics

#### **ORDERING INFORMATION TABLE**

Device code

VS- 10 RIA 120 M S90

1 2 3 4 5 6

1 - Vishay Semiconductors product

- Current code

3 - Essential part number

Voltage code x 10 = V<sub>RRM</sub> (see Voltage Ratings table)

5 - None = stud base TO-48 (TO-208AA) 1/4" 28UNF-2A

M = stud base TO-48 (TO-208AA) M6 x 1

6 - Critical dV/dt:

None = 300 V/µs (standard value)

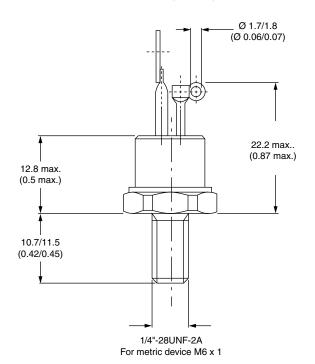
S90 = 1000 V/µs (special selection)

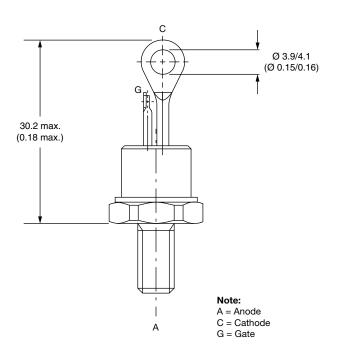
LINKS TO RELAT	ED DOCUMENTS
Dimensions	www.vishay.com/doc?95333

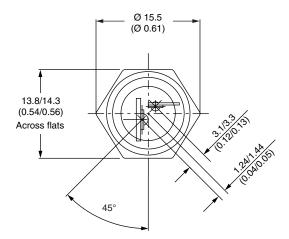


# TO-208AA (TO-48)

### **DIMENSIONS** in millimeters (inches)









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